
2SA1485

Silicon PNP Epitaxial

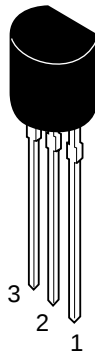
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Application

Low frequency amplifier

Outline

TO-92 (1)



- 1. Emitter
- 2. Collector
- 3. Base

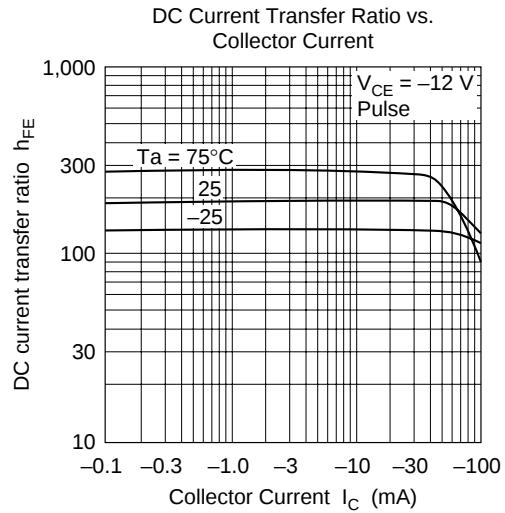
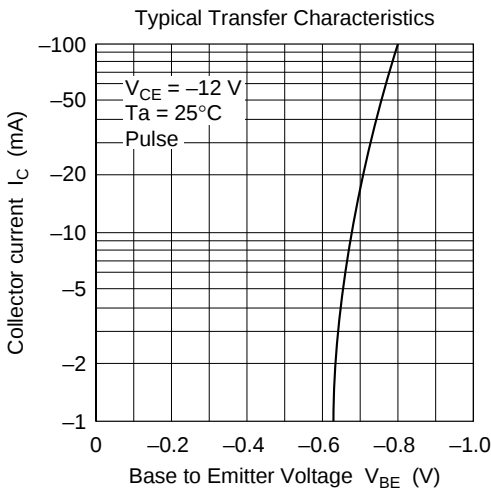
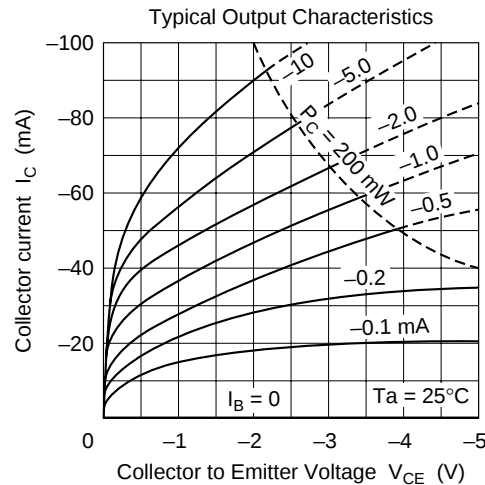
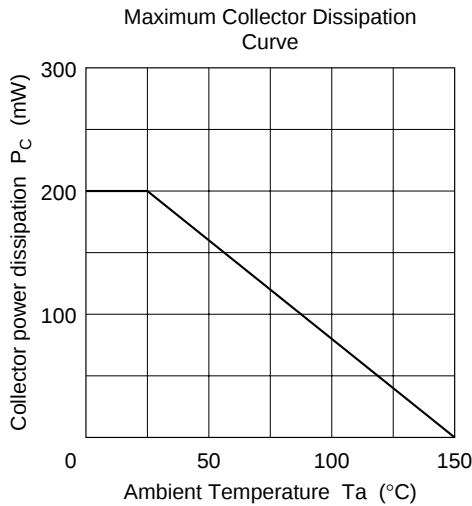
Absolute Maximum Ratings (Ta = 25°C)

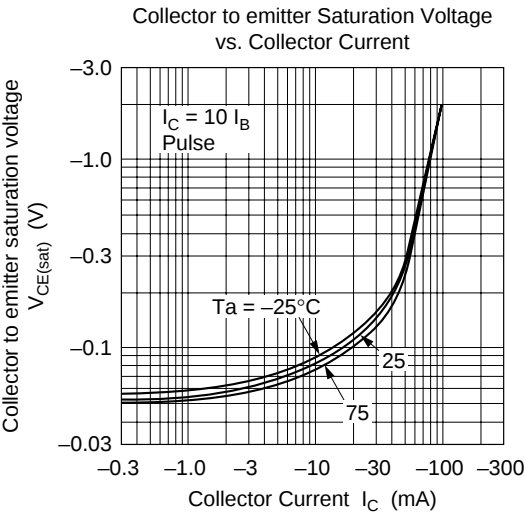
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-200	V
Collector to emitter voltage	V_{CEO}	-200	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

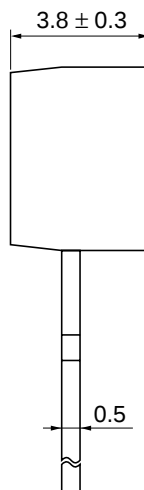
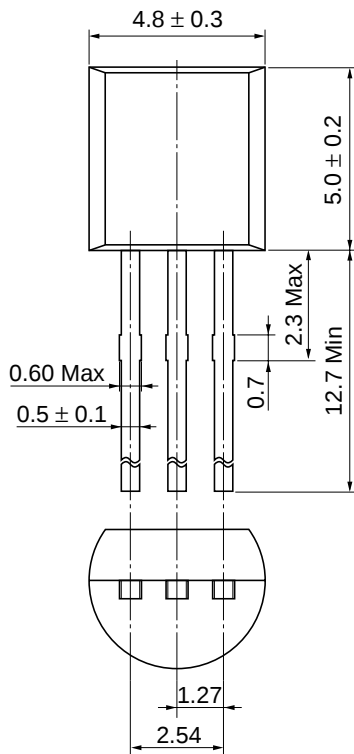
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-200	—	—	V	$I_C = -10\text{ }\mu\text{A}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-200	—	—	V	$I_C = -0.5\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	V	$I_E = -10\text{ }\mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CEO}	—	—	-500	μA	$V_{CE} = -200\text{ V}$, $R_{BE} = \infty$
DC current transfer ratio	h_{FE}	100	—	250		$V_{CE} = -12\text{ V}$, $I_C = -2\text{ mA}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.5	V	$I_C = -30\text{ mA}$, $I_B = -3\text{ mA}^{*1}$
Base to emitter voltage	V_{BE}	—	—	-1.0	V	$V_{CE} = -12\text{ V}$, $I_C = -2\text{ mA}^{*1}$

Note: 1. Pulse test







Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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